TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHCT574AF,TC74VHCT574AFW,TC74VHCT574AFT

Octal D-Type Flip-Flop with 3-State Output

The TC74VHCT574A is an advanced high speed CMOS OCTAL FLIP-FLOP with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The input voltage are compatible with TTL output voltage.

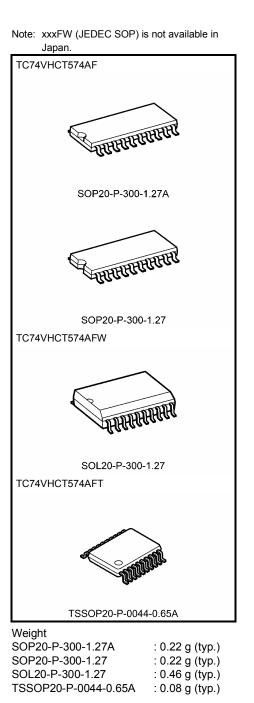
This device may be used as a level converter for interfacing 3.3 V to 5 V system.

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output ^(Note) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

Note: Output in off-state

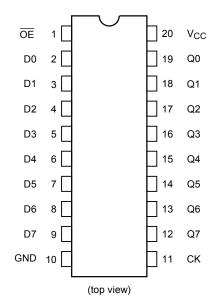
Features

- High speed: $f_{max} = 140 \text{ MHz}$ (typ.) at VCC = 5 V
- Low power dissipation: $ICC = 4 \mu A \pmod{at Ta} = 25^{\circ}C$
- Compatible with TTL outputs: VIL = 0.8 V (max)
 - $V_{IH} = 2.0 V (min)$
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Low noise: VOLP = 1.6 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 574 type.



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Pin Assignment



IEC Logic Symbol

0E <u>(1)</u> CK <u>(11)</u>	EN > C1		
D0 (2) D1 (3) D2 (4) D3 (5) D4 (6) D5 (7) D6 (8) D7 (9)	1D		(19) Q0 (18) Q1 (17) Q2 (16) Q3 (15) Q4 (14) Q5 (13) Q6 (12) Q7

Truth Table

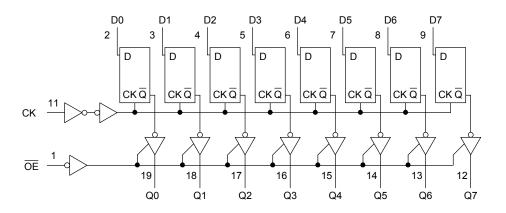
Inputs			Output
ŌE	СК	D	Output
Н	Х	Х	Z
L		Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Qn: No change

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 7.0	V
DC input voltage	V _{IN}	-0.5 to 7.0	V
DC output voltage	Vaur	-0.5 to 7.0 (Note 2)	V
	Vout	-0.5 to V _{CC} + 0.5 (Note 3)	v
Input diode current	IIK	-20	mA
Output diode current	I _{OK}	±20 (Note 4)	mA
DC output current	IOUT	±25	mA
DC V _{CC} /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: Output in off-state

Note 3: High or low state. $I_{\mbox{OUT}}$ absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Conditions (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5 to 5.5	V
Input voltage	V _{IN}	0 to 5.5	V
Output veltage	V _{OUT}	0 to 5.5 (Note 2)	V
Output voltage		0 to V _{CC} (Note 3)	v
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dV	0 to 20	ns/V

Note 1: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Output in off-state

Note 3: High or low state

Electrical Characteristics

DC Characteristics

Characteristics	Symbol Test Condition			-	Га = 25°(0	Ta -40 to	Unit		
					Min	Тур.	Max	Min	Max	
High-level input voltage	V _{IH}		—		2.0	_	-	2.0	_	V
Low-level input voltage	V _{IL}		_	4.5 to 5.5		_	0.8	_	0.8	V
High-level output	Maria	V _{IN}	I _{OH} = -50 μA	4.5	4.40	4.50	_	4.40	—	V
voltage	VOH	= V _{IH} or V _{IL}	I _{OH} = −8 mA	4.5	3.94	—	—	3.80	—	v
Low-level output	M	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	4.5		0.0	0.10		0.10	V
voltage V _{OL}	VOL		I _{OL} = 8 mA	4.5	-	_	0.36		0.44	v
3-state output off-state current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5	_	_	±0.25	_	±2.50	μA
Input leakage current	I _{IN}	V _{IN} = 5.5	V _{IN} = 5.5 V or GND		_	_	±0.1	_	±1.0	μA
	I _{CC}	$V_{IN} = V_C$	_C or GND	5.5	_	_	4.0	-	40.0	μA
Quiescent supply current	Ісст	Per input: V _{IN} = 3.4 V Other input: V _{CC} or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage current	IOPD	Vout = 5	5.5 V	0	_	_	+0.5	_	+5.0	μA

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	_	Ta = 25°C		Ta = -40 to 85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width (CK)	t _{w (H)} t _{w (L)}	-	5.0 ± 0.5	_	6.5	8.5	ns
Minimum set-up time	ts	_	5.0 ± 0.5	_	2.5	2.5	ns
Minimum hold time	t _h	—	5.0 ± 0.5	_	2.5	2.5	ns

AC Characteristics (input: t_r = t_f = 3 ns)

Characteristics	Symbol		st Condition		Ta = 25°C			Ta = −40 to 85°C		Unit
	- ,		$V_{CC}(V)$	C _L (pF)	Min	Тур.	Max	Min	Max	
Propagation delay time	t _{pLH}	_	5.0 ± 0.5	15		4.1	9.4	1.0	10.5	ns
(CK-Q)	t _{pHL}		0.0 1 0.0	50	—	5.6	10.4	1.0	11.5	110
3-state output enable	t _{pZL}	R _L = 1 kΩ	5.0 ± 0.5	15		6.5	10.2	1.0	11.5	ns
time	t _{pZH}		5.0 ± 0.5	50	-	7.3	11.2	1.0	12.5	115
3-state output disable time	t _{pLZ} t _{pHZ}	R _L = 1 kΩ	5.0 ± 0.5	50	_	7.0	11.2	1.0	12.0	ns
Maximum clock	£	— 5.0 ± 0.5	50.05	15	90	140		80	_	MHz
frequency	f _{max}		50	85	130	_	75	_	IVITIZ	
Output to output skew	t _{osLH} t _{osHL}	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input capacitance	CIN		_			4	10		10	pF
Output capacitance	C _{OUT}		_		_	9	_	_		pF
Power dissipation capacitance	C _{PD}			(Note 2)	_	25	_	_	_	pF

Note 1: Parameter guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$

And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

C_{PD} (total) = 14 + 11 ⋅ n

Noise Characteristics (input: t_r = t_f = 3 ns) (Note)

Characteristics	Symbol	Test Condition		Ta =	Unit	
Characteristics	Symbol		V _{CC} (V)	Тур.	Max	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	1.1	1.5	v
				(1.2)	(1.6)	
Quiet output minimum dynamic V _{OL}	Marrie	C _I = 50 pF	5.0	-1.1	-1.5	V
	VOLV	CL - 50 PF	5.0	(-1.2)	(-1.6)	v
Minimum high level dynamic input voltage	V _{IHD}	C _L = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage	V _{ILD}	C _L = 50 pF	5.0	—	0.8	V

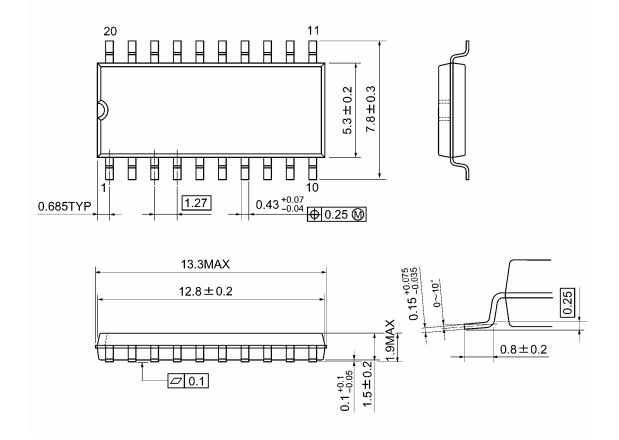
Note: The value in () only applies to JEDEC SOP (FW) devices.

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Package Dimensions

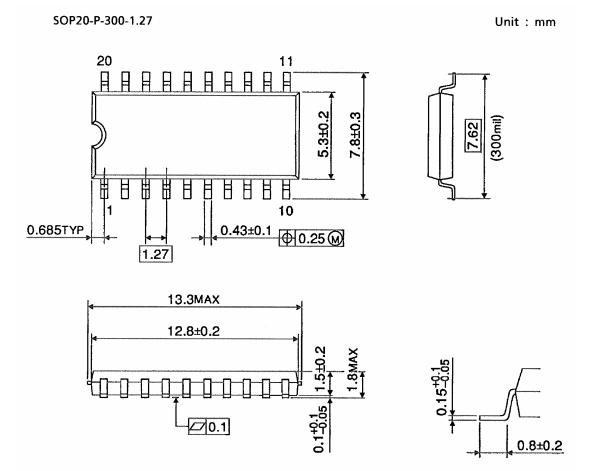
SOP20-P-300-1.27A

Unit: mm



Weight: 0.22 g (typ.)

Package Dimensions

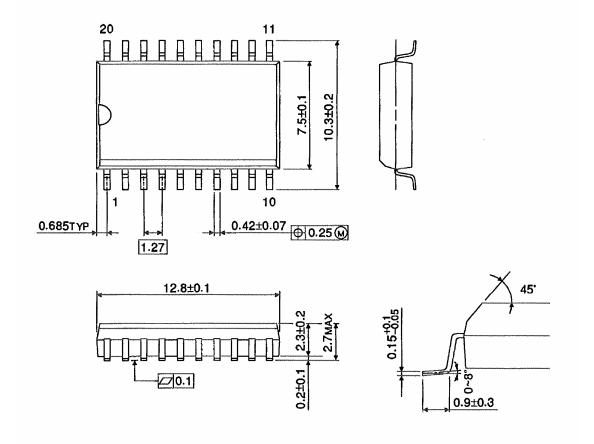


Weight: 0.22 g (typ.)

Package Dimensions (Note)

SOL20-P-300-1.27

Unit : mm

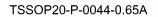


Note: This package is not available in Japan.

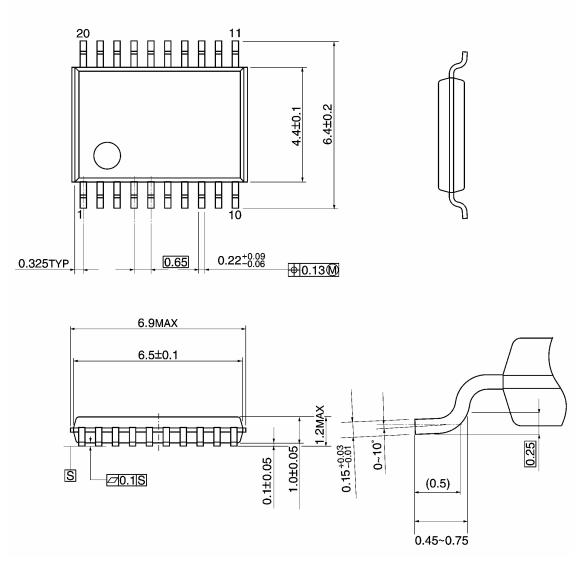
Weight: 0.46 g (typ.)

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Package Dimensions



Unit: mm



Weight: 0.08 g (typ.)

Note: Lead (Pb)-Free Packages SOP20-P-300-1.27A TSSOP20-P-0044-0.65A

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